



STN3NE06

N - CHANNEL 60V - 0.08Ω - 3A - SOT-223 STripFET™ POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STN3NE06	60 V	< 0.100 Ω	3 A

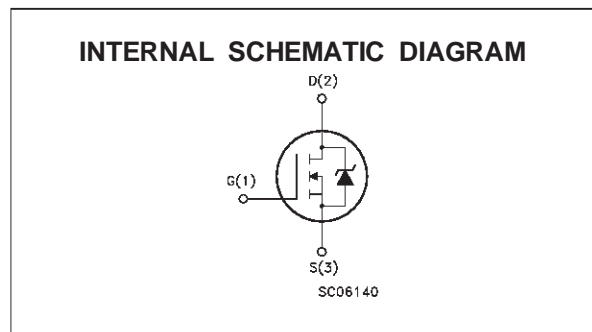
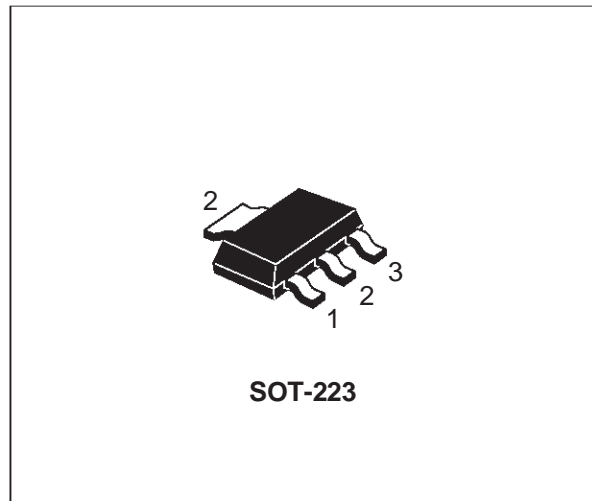
- TYPICAL R_{DS(on)} = 0.08 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- AVALANCHE RUGGED TECHNOLOGY
- 100 % AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION

DESCRIPTION

This Power Mosfet is the latest development of STMicroelectronics unique "Single Feature Size™" stip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- DC MOTOR CONTROL (DISK DRIVES, etc.)
- DC-DC & DC-AC CONVERTERS
- SYNCHRONOUS RECTIFICATION



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	60	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	60	V
V _{GS}	Gate-source Voltage	± 20	V
I _D	Drain Current (continuous) at T _c = 25 °C	3	A
I _D	Drain Current (continuous) at T _c = 100 °C	1.8	A
I _{DM} (•)	Drain Current (pulsed)	12	A
P _{tot}	Total Dissipation at T _c = 25 °C	2.5	W
	Derating Factor	0.02	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	6	V/ns
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area
New RDS (on) spec. starting from JULY 98

(1) I_{SD} ≤ 12 A, di/dt ≤ 200 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

STN3NE06

THERMAL DATA

$R_{thj-pcb}$	Thermal Resistance Junction-PC Board	Max	50	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-ambient (Surface Mounted)	Max	60	$^{\circ}C/W$
T_j	Maximum Lead Temperature For Soldering Purpose		260	$^{\circ}C$

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	3	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}C$, $I_D = I_{AR}$, $V_{DD} = 25 V$)	20	mJ

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250 \mu A$ $V_{GS} = 0$	60			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$ $T_c = 125^{\circ}C$			1 10	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20 V$			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250 \mu A$	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10 V$ $I_D = 6A$		0.080	0.100	Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10 V$	3			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 1.5 A$	1	3		S
C_{iss}	Input Capacitance	$V_{DS} = 25 V$ $f = 1 MHz$ $V_{GS} = 0 V$		760	1000	pF
C_{oss}	Output Capacitance			100	140	pF
C_{rss}	Reverse Transfer Capacitance			30	45	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 30\text{ V}$ $I_D = 6\text{ A}$		10	15	ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		35	50	ns
Q_g	Total Gate Charge	$V_{DD} = 40\text{ V}$ $I_D = 12\text{ A}$ $V_{GS} = 10\text{ V}$		20	25	nC
Q_{gs}	Gate-Source Charge			5		nC
Q_{gd}	Gate-Drain Charge			7		nC

SWITCHING OFF

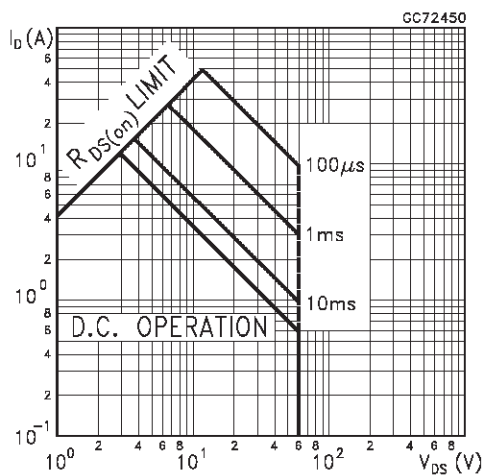
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(off)}$	Off-voltage Rise Time	$V_{DD} = 48\text{ V}$ $I_D = 12\text{ A}$		7	10	ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		18	25	ns
t_c	Cross-over Time			30	45	ns

SOURCE DRAIN DIODE

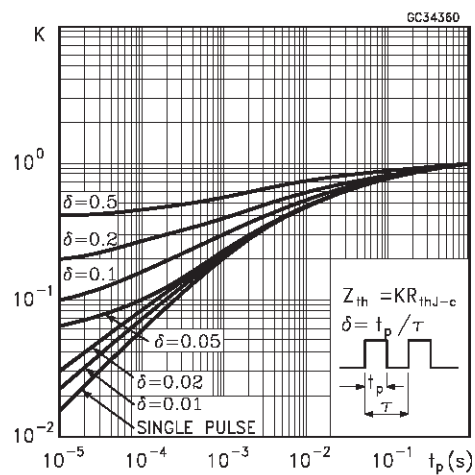
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				3	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				12	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 3\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 12\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		65		ns
Q_{rr}	Reverse Recovery Charge			0.18		μC
I_{RRM}	Reverse Recovery Current			5.5		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %
 (•) Pulse width limited by safe operating area

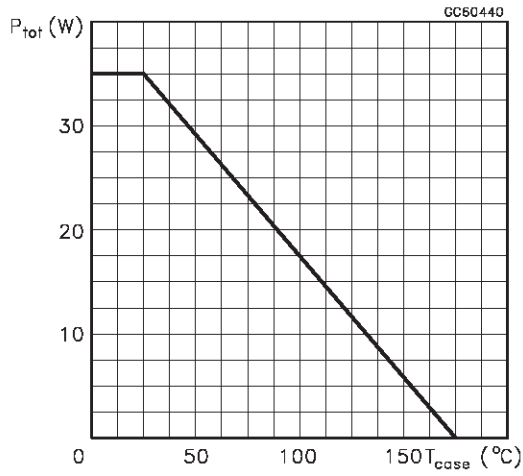
Safe Operating Area



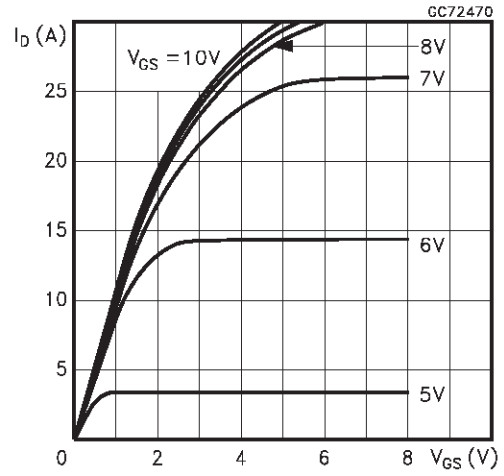
Thermal Impedance



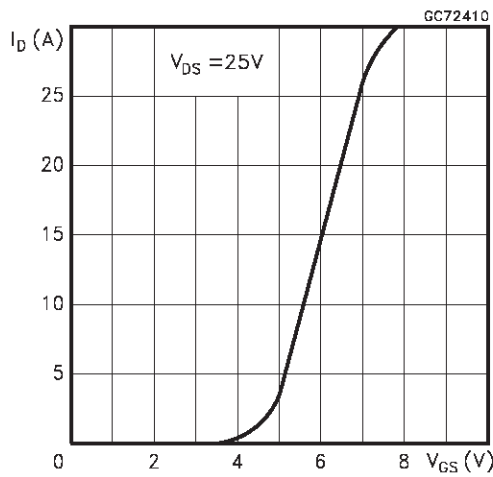
Derating Curve



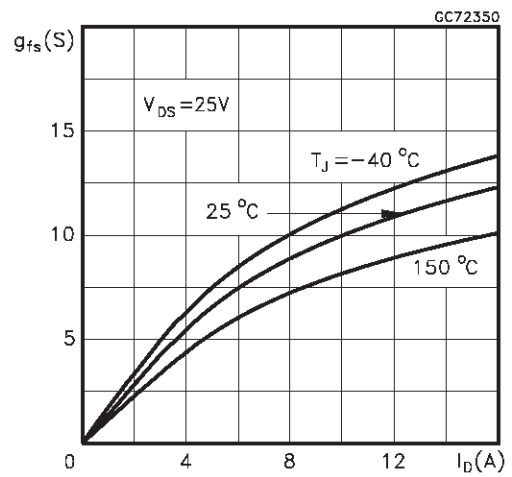
Output Characteristics



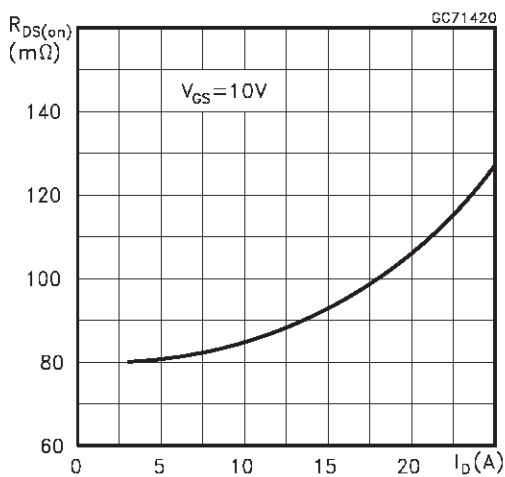
Transfer Characteristics



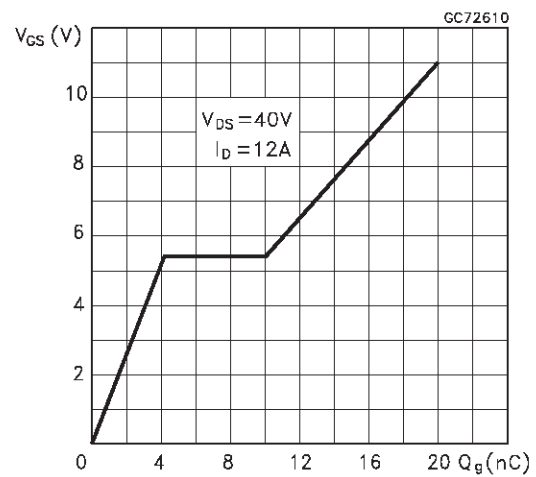
Transconductance



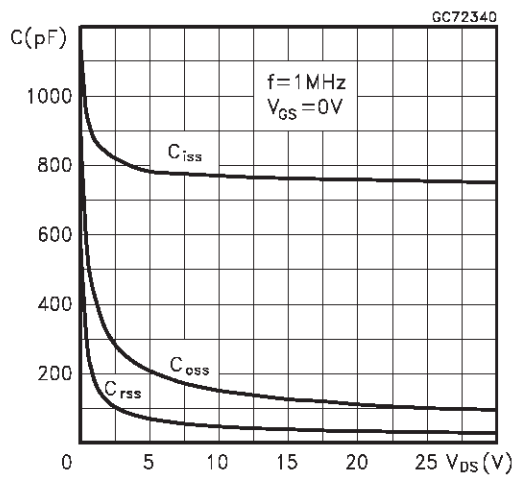
Static Drain-source On Resistance



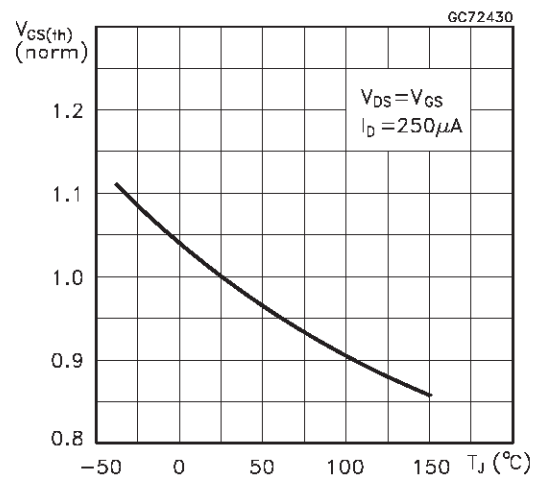
Gate Charge vs Gate-source Voltage



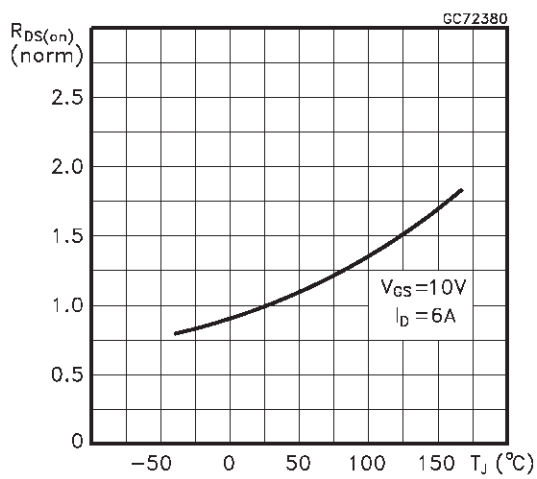
Capacitance Variations



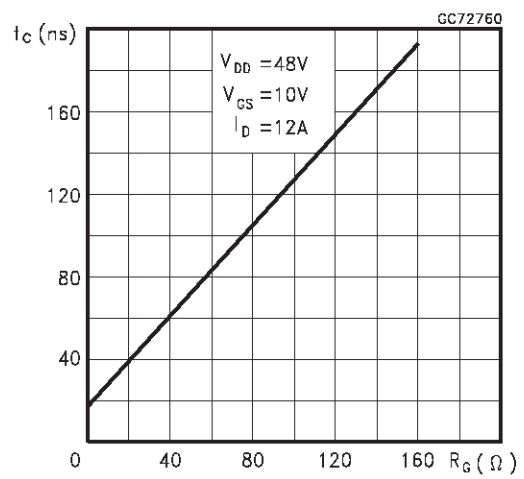
Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Cross-over Time



Source-drain Diode Forward Characteristics

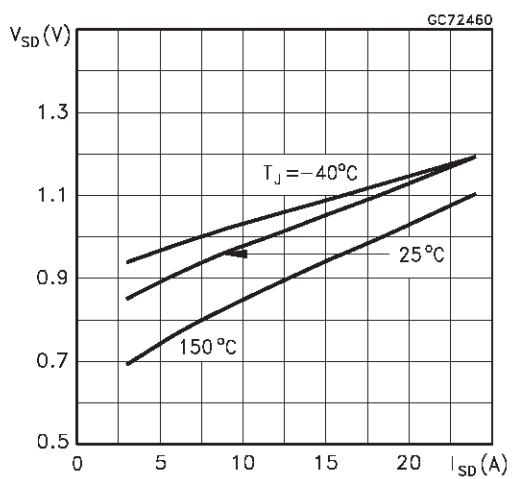


Fig. 1: Unclamped Inductive Load Test Circuit

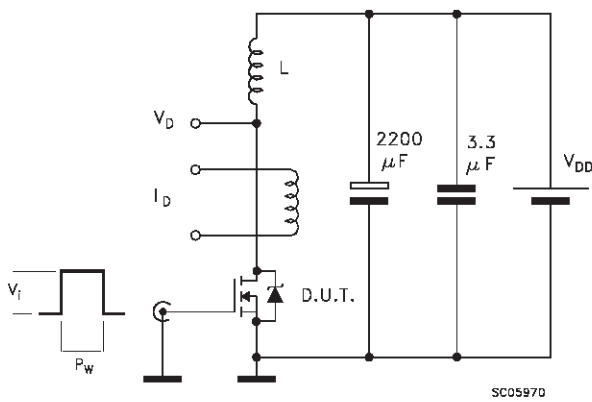


Fig. 2: Unclamped Inductive Waveform

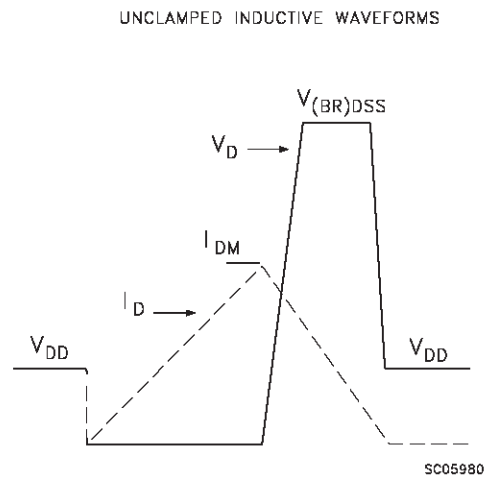


Fig. 3: Switching Times Test Circuits For Resistive Load

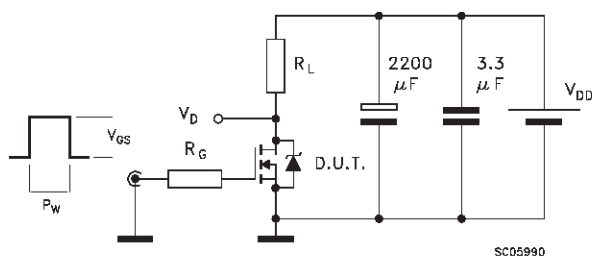


Fig. 4: Gate Charge test Circuit

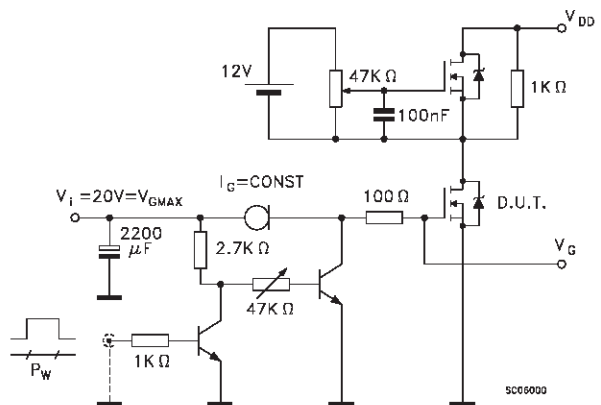
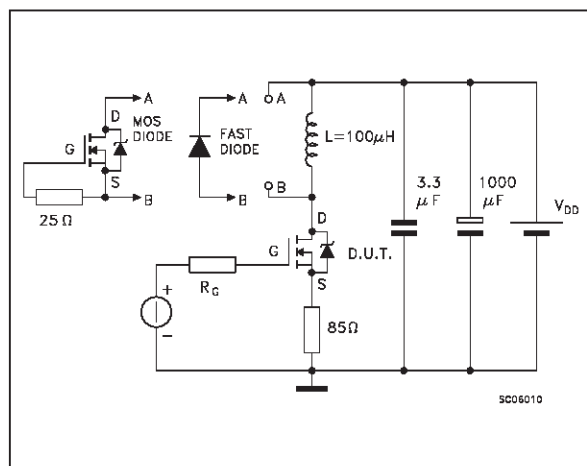
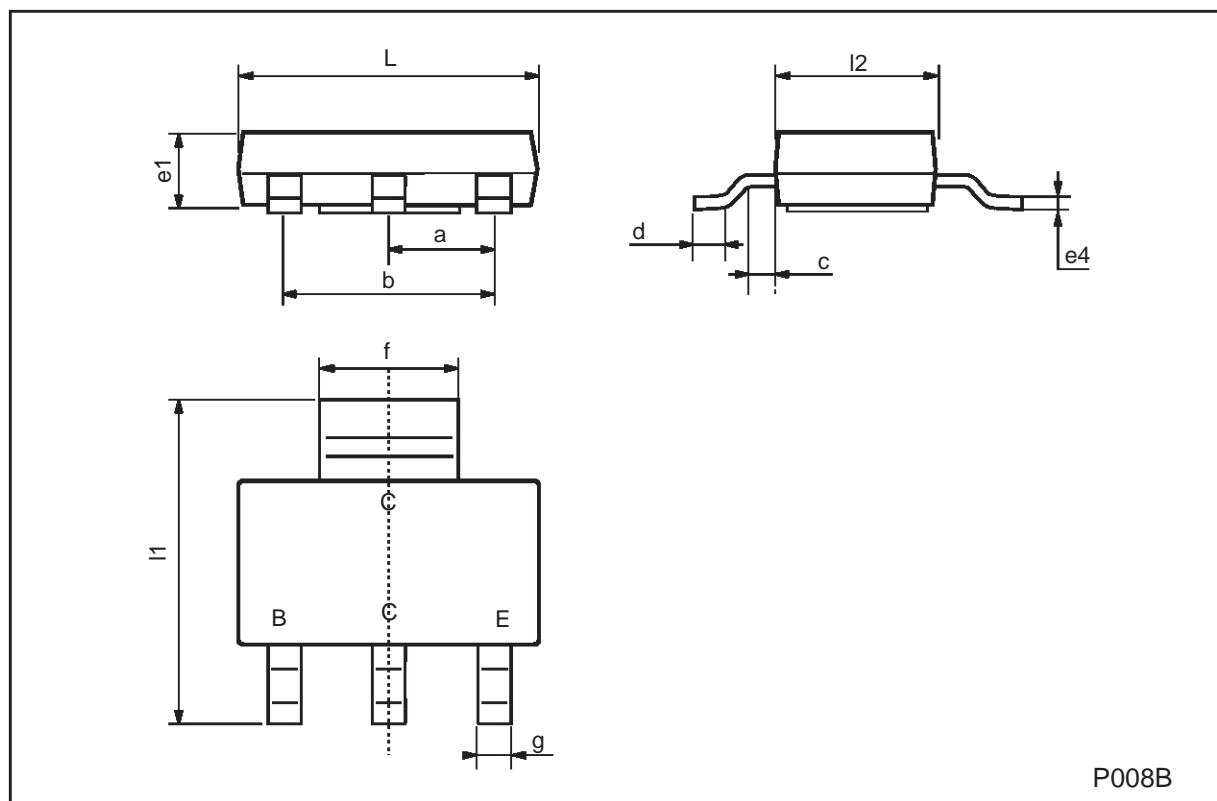


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



SOT-223 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a	2.27	2.3	2.33	89.4	90.6	91.7
b	4.57	4.6	4.63	179.9	181.1	182.3
c	0.2	0.4	0.6	7.9	15.7	23.6
d	0.63	0.65	0.67	24.8	25.6	26.4
e1	1.5	1.6	1.7	59.1	63	66.9
e4			0.32			12.6
f	2.9	3	3.1	114.2	118.1	122.1
g	0.67	0.7	0.73	26.4	27.6	28.7
l1	6.7	7	7.3	263.8	275.6	287.4
l2	3.5	3.5	3.7	137.8	137.8	145.7
L	6.3	6.5	6.7	248	255.9	263.8



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